

MOSFETs Silicon Carbide N-Channel MOS

TW083U65C

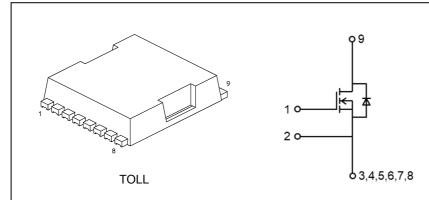
1. Applications

• Switching Voltage Regulators

2. Features

- (1) Chip design of 3rd generation (Built-in SiC schottky barrier diode)
- (2) Low diode forward voltage: $V_{DSF} = -1.35 \text{ V (typ.)}$
- (3) High voltage: $V_{DSS} = 650 \text{ V}$
- (4) Low drain-source on-resistance: $R_{DS(ON)} = 83 \text{ m}\Omega$ (typ.)
- (5) Less susceptible to malfunction due to high threshold voltage: V_{th} = 3.0 to 5.0 V (V_{DS} = 10 V, I_D = 0.6 mA)
- (6) Recommended gate source drive voltage: $V_{GS_on} = 18 \text{ V}$, $V_{GS_off} = 0 \text{ V}$
- (7) Enhancement mode.

3. Packaging and Internal Circuit



- 1: Gate
- 2: Source 1
- 3, 4, 5, 6, 7, 8: Source 2
- 9: Drain (heatsink)

Notice: Only use source 1 pin for gate input signal return. Recommended for using source 1 pin due to reducing the influence of inductance. Please make sure that the main current flows into the source 2 pin.



4. Absolute Maximum Ratings (Note) (T_a = 25 °C unless otherwise specified)

(Characteristics		Symbol	Rating	Unit
Drain-source voltage			V_{DSS}	650	V
Gate-source voltage			V _{GSS}	+25/-10	
Drain current (DC)	(T _c = 25 °C)	(Note 1)	I _D	28	Α
Drain current (DC)	(T _c = 100°C)	(Note 1)	I _D	20	
Drain current (pulsed)	(T _c = 25 °C)	(Note 1)	I _{DP}	66	
Drain current (pulsed)	(T _c = 100°C)	(Note 1)	I _{DP}	52	
Power dissipation	(T _c = 25°C)		P_{D}	111	W
Channel temperature			T _{ch}	175	℃
Storage temperature			T _{stg}	-55 to 175	

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

5. Thermal Characteristics

Characteristics	Symbol	Max	Unit
Channel-to-case thermal resistance		1.350	°C/W

Note 1: Ensure that the channel temperature does not exceed 175 °C.

Note: This transistor is sensitive to electrostatic discharge and should be handled with care. It should be used for switching applications.



6. Electrical Characteristics

6.1. Static Characteristics ($T_a = 25$ °C unless otherwise specified)

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current		I _{GSS}	V _{GS} = +25/-10 V, V _{DS} = 0 V	_	_	±0.1	μА
Drain cut-off current		I _{DSS}	V _{DS} = 650 V, V _{GS} = 0 V	_	2.8	37	
			T _a = 150 °C, V _{DS} = 650 V, V _{GS} = 0 V	_	14	_	
Drain-source breakdown voltage		V _{(BR)DSS}	I _D = 4 mA, V _{GS} = 0 V	650	_	_	V
Gate threshold voltage	(Note 2)	V _{th}	V _{DS} = 10 V, I _D = 0.6 mA	3.0	_	5.0	
Drain-source on-resistance		R _{DS(ON)}	V _{GS} = 18 V, I _D = 15 A	_	83	124	mΩ
			T _a = 150 °C, V _{GS} = 18 V, I _D = 15 A	_	89	_	

Note 2: Please be sure to apply I_{GSS} (V_{GS} = 25 V) before the V_{th} test.



6.2. Dynamic Characteristics (T_a = 25 °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance	C _{iss}	V _{DS} = 400 V, V _{GS} = 0 V,	_	873	_	pF
Reverse transfer capacitance	C _{rss}	f = 100 kHz	_	3.4	_	
Output capacitance	C _{oss}	1	_	110	_	
Effective output capacitance (energy related)	C _{o(er)}		_	125	_	
Effective output capacitance (time related)	C _{o(tr)}		_	180		
Output charge	Q _{oss}		_	72	_	nC
C _{oss} stored energy	E _{oss}	1	_	10	_	μJ
Gate resistance	r _g	V _{DS} = OPEN, f = 1 MHz	_	4.4	_	Ω
Turn-on delay time	t _{d(on)}	See Fig. 6.2.1	_	21	_	ns
Switching time (rise time)	t _r		_	14	_	
Turn-off delay time	t _{d(off)}		_	28	_	
Switching time (fall time)	t _f		_	14	_	
Turn-on switching loss	E _{on}			98		μJ
Turn-off switching loss	E _{off}]	_	38	_	

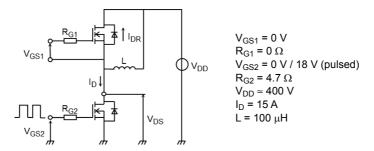


Fig. 6.2.1 Switching Time Test Circuit

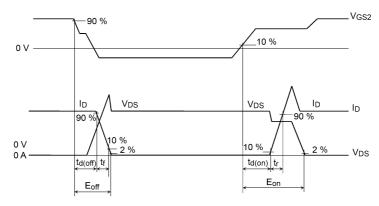


Fig. 6.2.2 Timing Diagrams



6.3. Gate Charge Characteristics ($T_a = 25$ °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus gate-drain)	9	$V_{DD} \approx 400 \text{ V}, V_{GS} = 18 \text{ V},$ $I_{D} = 15 \text{ A}$	_	28		nC
Gate-source charge 1	Q _{gs1}			14		
Gate-drain charge	Q _{gd}		_	3.9	_	

6.4. Source \cdot Drain Characteristics (T_a = 25 °C unless otherwise specified)

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit		
Reverse drain current (DC)	(Note 3)	(Note 3)	DC) (Note 3)	rain current (DC) (Note 3) I_{DR} $T_c = 25 ^{\circ}\text{C}, V_{GS} = -5 ^{\circ}\text{V}$	$T_c = 25 ^{\circ}\text{C}, V_{GS} = -5 ^{\circ}\text{V}$	_	_	26	Α
			T _c = 100 °C, V _{GS} = -5 V	_	_	17			
			T _c = 25 °C, V _{GS} = 18 V	_	_	28			
			T _c = 100 °C, V _{GS} = 18 V	_	_	20			
Reverse drain current	(Note 3)	I _{DRP}	T _c = 25 °C, V _{GS} = -5 V	_	_	66			
(pulsed)			T _c = 100 °C, V _{GS} = -5 V	_	_	29			
			T _c = 25 °C, V _{GS} = 18 V	_	_	66			
			T _c = 100 °C, V _{GS} = 18 V	_	_	52			
Diode forward voltage		V _{DSF}	I _{DR} = 8 A, V _{GS} = -5 V	_	-1.35	-1.80	V		
			T _a = 150 °C, I _{DR} = 8 A, V _{GS} = -5 V	_	-1.57	_			
Reverse recovery time		t _{rr}	I _{DR} = 10 A, V _{GS} = 0 V,	_	45	_	ns		
Reverse recovery charge		Q _{rr}	V _{DD} = 400 V, -dl _{DR} /dt = 1000 A/μs	_	189	_	nC		
Peak reverse recovery current		I _{rr}		_	8.4	_	А		

Note 3: Ensure that the channel temperature does not exceed 175 $^{\circ}\text{C}$.

Rev.1.0



7. Marking (Note)

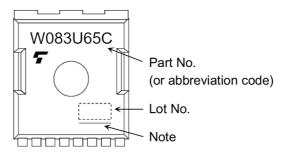


Fig. 7.1 Marking

Note: A line under a Lot No. identifies the indication of product Labels.

Not underlined: [[Pb]]/INCLUDES > MCV

Underlined: [[G]]/RoHS COMPATIBLE or [[G]]/RoHS [[Pb]]

Please contact your TOSHIBA sales representative for details as to environmental matters such as the RoHS compatibility of Product.

The RoHS is the Directive 2011/65/EU of the European Parliament and of the Council of 8 June 2011 on the restriction of the use of certain hazardous substances in electrical and electronic equipment.



8. Characteristics Curves (Note)

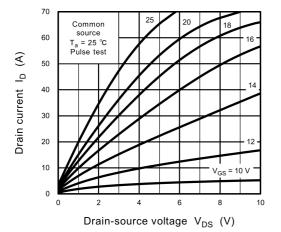


Fig. 8.1 I_D - V_{DS}

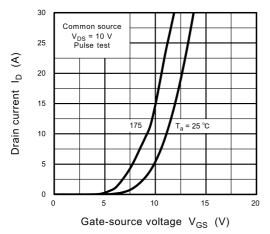


Fig. 8.3 I_D - V_{GS}

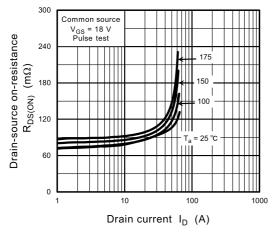


Fig. 8.5 R_{DS(ON)} - I_D

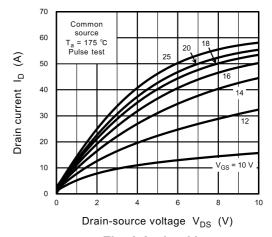


Fig. 8.2 I_D - V_{DS}

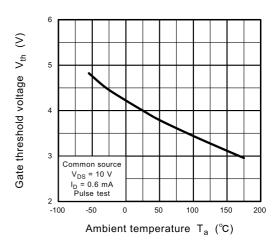


Fig. 8.4 V_{th} - T_a

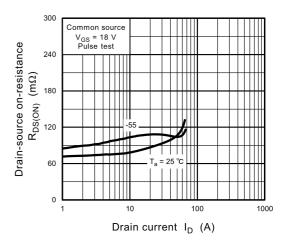


Fig. 8.6 R_{DS(ON)} - I_D



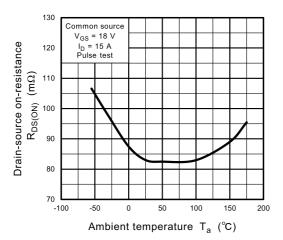


Fig. 8.7 R_{DS(ON)} - T_a

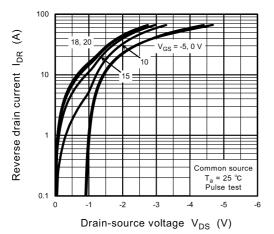


Fig. 8.9 I_{DR} - V_{DS}

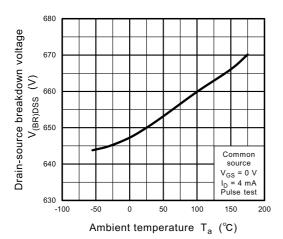


Fig. 8.11 V_{(BR)DSS} - T_a

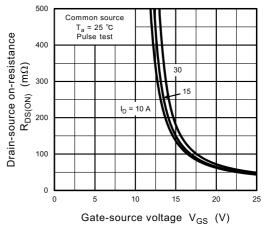


Fig. 8.8 R_{DS(ON)} - V_{GS}

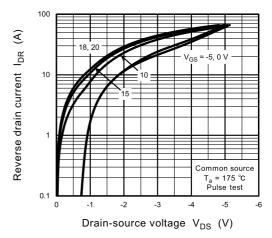


Fig. 8.10 I_{DR} - V_{DS}

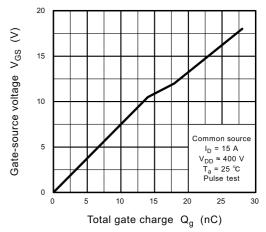


Fig. 8.12 Dynamic Input Characteristics



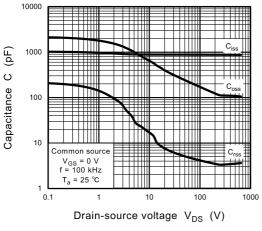


Fig. 8.13 C - V_{DS}

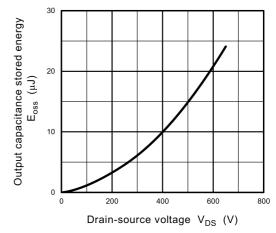


Fig. 8.14 E_{oss} - V_{DS}

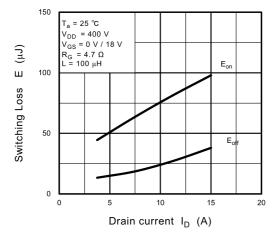


Fig. 8.15 E - I_D

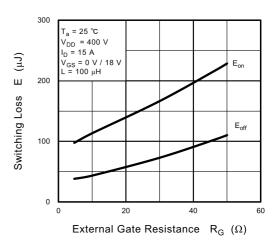


Fig. 8.16 E - R_G

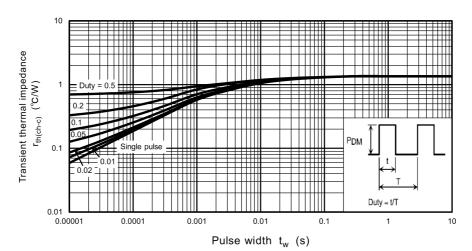
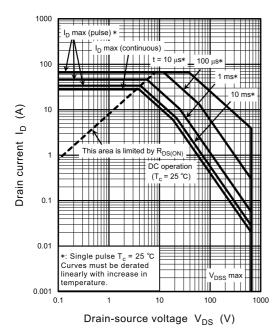


Fig. 8.17 $r_{th(ch-c)} - t_w$ (Guaranteed Maximum)





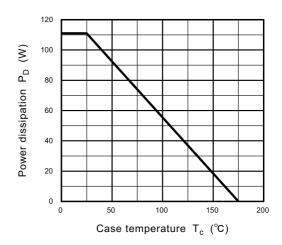


Fig. 8.18 Safe Operating Area (Guaranteed Maximum)

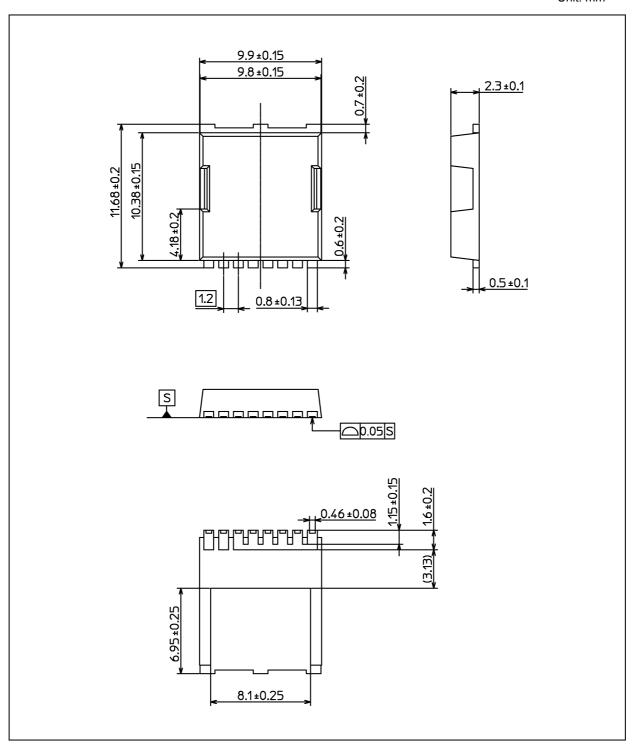
Fig. 8.19 P_D - T_c (Guaranteed Maximum)

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



Package Dimensions

Unit: mm



Weight: 0.75 g (typ.)

Package Name(s)				
TOSHIBA: 2-10AF1A				
Nickname: TOLL				



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